

## N-Channel 100-V (D-S) MOSFET

### PRODUCT SUMMARY

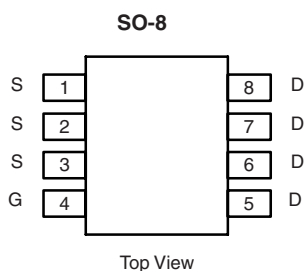
| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) |
|--------------|---------------------------|-----------|
| 100          | 0.060 at $V_{GS} = 10$ V  | 4.6       |
|              | 0.080 at $V_{GS} = 6$ V   | 4.0       |

### FEATURES

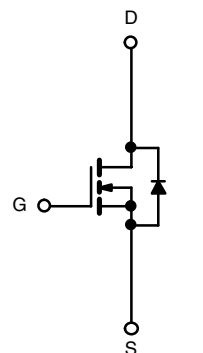
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



**Ordering Information:** Si4482DY-T1-E3 (Lead (Pb)-free)  
Si4482DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

| Parameter                                                 | Symbol         | Limit       | Unit |
|-----------------------------------------------------------|----------------|-------------|------|
| Drain-Source Voltage                                      | $V_{DS}$       | 100         | V    |
| Gate-Source Voltage                                       | $V_{GS}$       | $\pm 20$    |      |
| Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>   | $I_D$          | 4.6         | A    |
|                                                           |                | 3.7         |      |
| Pulsed Drain Current                                      | $I_{DM}$       | 40          |      |
| Continuous Source Current (Diode Conduction) <sup>a</sup> | $I_S$          | 2.1         |      |
| Maximum Power Dissipation <sup>a</sup>                    | $P_D$          | 2.5         | W    |
|                                                           |                | 1.6         |      |
| Operating Junction and Storage Temperature Range          | $T_J, T_{stg}$ | - 55 to 150 | °C   |

### THERMAL RESISTANCE RATINGS

| Parameter                                | Symbol     | Limit | Unit |
|------------------------------------------|------------|-------|------|
| Maximum Junction-to-Ambient <sup>a</sup> | $R_{thJA}$ | 50    | °C/W |

Notes:

a. Surface Mounted on FR4 board,  $t \leq 10$  s.

| <b>SPECIFICATIONS</b> $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted |              |                                                                                                                                 |      |                   |           |               |
|-----------------------------------------------------------------------------------|--------------|---------------------------------------------------------------------------------------------------------------------------------|------|-------------------|-----------|---------------|
| Parameter                                                                         | Symbol       | Test Conditions                                                                                                                 | Min. | Typ. <sup>a</sup> | Max.      | Unit          |
| <b>Static</b>                                                                     |              |                                                                                                                                 |      |                   |           |               |
| Gate Threshold Voltage                                                            | $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$                                                                              | 2    |                   |           | V             |
| Gate-Body Leakage                                                                 | $I_{GSS}$    | $V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$                                                                              |      |                   | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current                                                   | $I_{DSS}$    | $V_{DS} = 100\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                 |      |                   | 1         | $\mu\text{A}$ |
|                                                                                   |              | $V_{DS} = 100\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 55\text{ }^{\circ}\text{C}$                                            |      |                   | 20        |               |
| On-State Drain Current <sup>b</sup>                                               | $I_{D(on)}$  | $V_{DS} = 5\text{ V}$ , $V_{GS} = 10\text{ V}$                                                                                  | 20   |                   |           | A             |
| Drain-Source On-State Resistance <sup>b</sup>                                     | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ , $I_D = 4.6\text{ A}$                                                                                   |      | 0.045             | 0.060     | $\Omega$      |
|                                                                                   |              | $V_{GS} = 6\text{ V}$ , $I_D = 4.0\text{ A}$                                                                                    |      | 0.050             | 0.080     |               |
| Forward Transconductance <sup>b</sup>                                             | $g_{fs}$     | $V_{DS} = 15\text{ V}$ , $I_D = 4.6\text{ A}$                                                                                   |      | 20                |           | S             |
| Diode Forward Voltage <sup>b</sup>                                                | $V_{SD}$     | $I_S = 2.1\text{ A}$ , $V_{GS} = 0\text{ V}$                                                                                    |      |                   | 1.2       | V             |
| <b>Dynamic<sup>a</sup></b>                                                        |              |                                                                                                                                 |      |                   |           |               |
| Total Gate Charge                                                                 | $Q_g$        | $V_{DS} = 50\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 4.6\text{ A}$                                                          |      | 30                | 50        | nC            |
| Gate-Source Charge                                                                | $Q_{gs}$     |                                                                                                                                 |      | 7.5               |           |               |
| Gate-Drain Charge                                                                 | $Q_{gd}$     |                                                                                                                                 |      | 7                 |           |               |
| Gate Resistance                                                                   | $R_g$        |                                                                                                                                 | 1    |                   | 4.4       | $\Omega$      |
| Turn-On Delay Time                                                                | $t_{d(on)}$  | $V_{DD} = 50\text{ V}$ , $R_L = 50\text{ }\Omega$<br>$I_D \cong 1\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 6\text{ }\Omega$ |      | 13                | 25        | ns            |
| Rise Time                                                                         | $t_r$        |                                                                                                                                 |      | 12                | 25        |               |
| Turn-Off Delay Time                                                               | $t_{d(off)}$ |                                                                                                                                 |      | 60                | 90        |               |
| Fall Time                                                                         | $t_f$        |                                                                                                                                 |      | 25                | 40        |               |
| Source-Drain Reverse Recovery Time                                                | $t_{rr}$     | $I_F = 2.1\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$                                                                       |      | 50                | 80        |               |

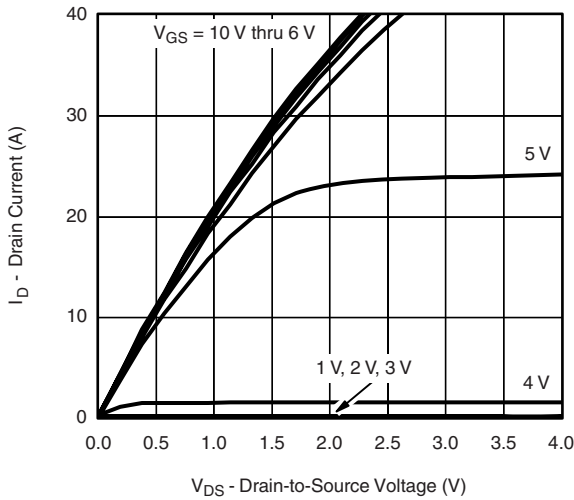
Notes:

a. For design aid only; not subject to production testing.

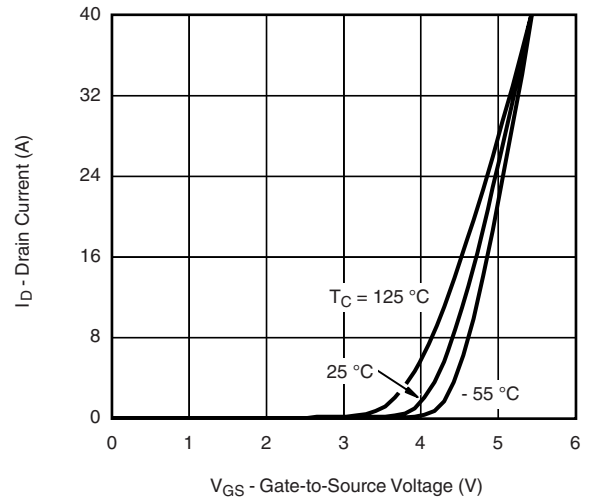
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

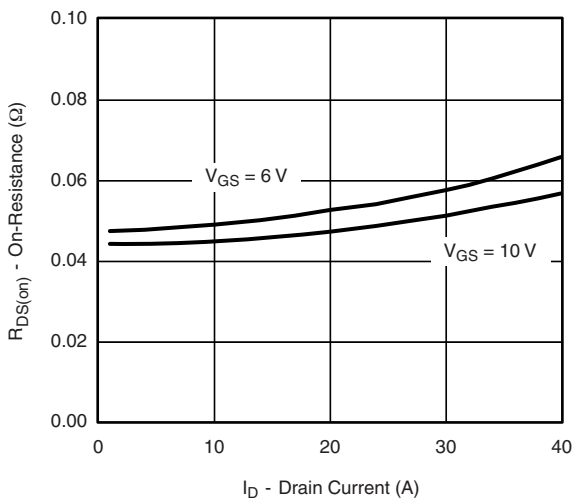
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



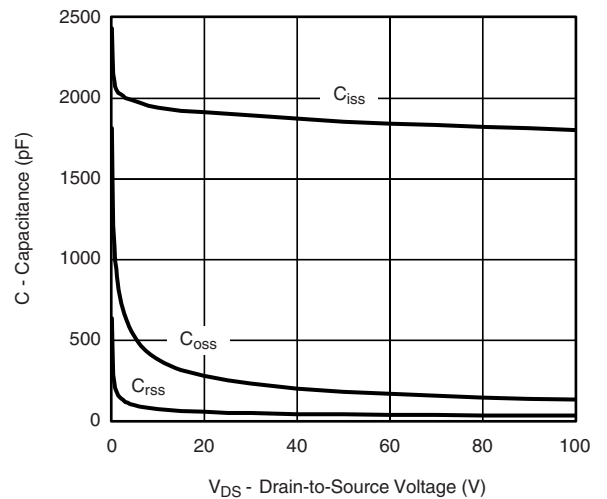
Output Characteristics



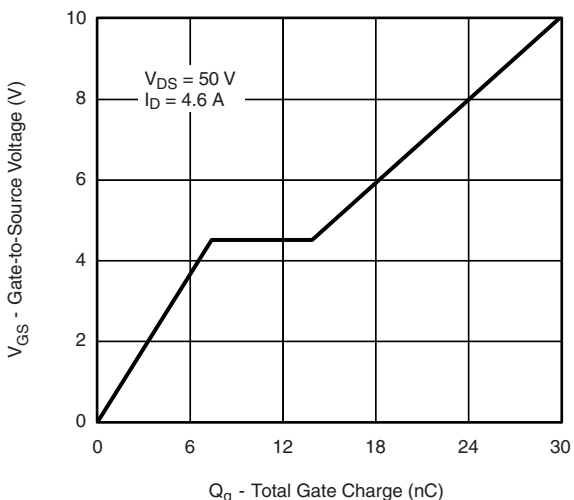
Transfer Characteristics



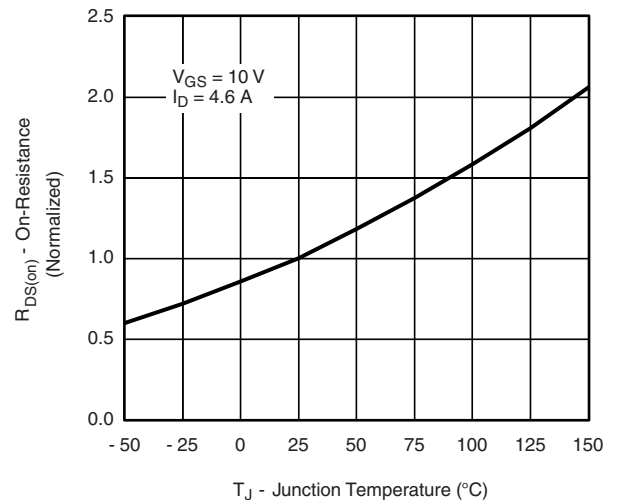
On-Resistance vs. Drain Current



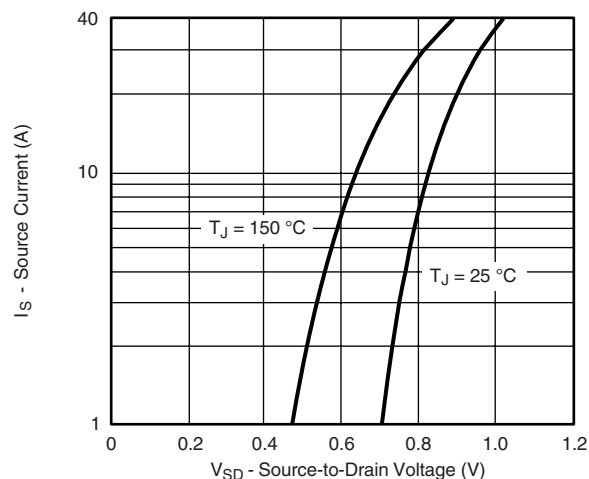
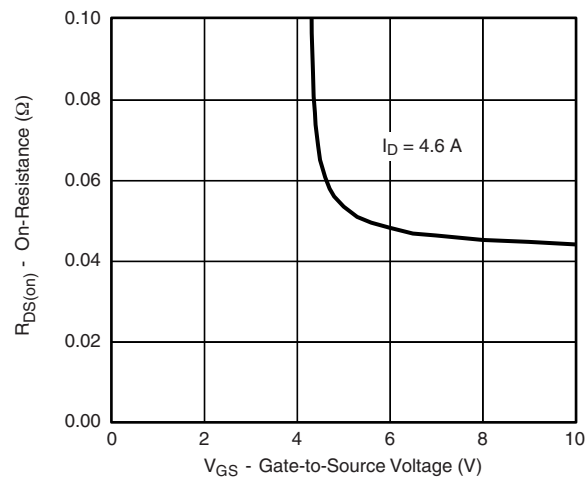
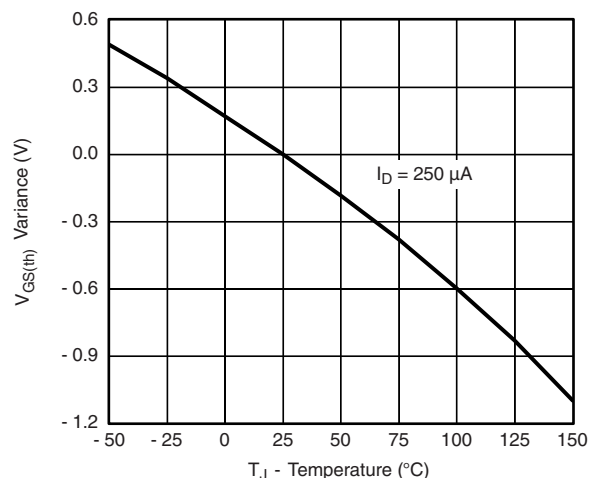
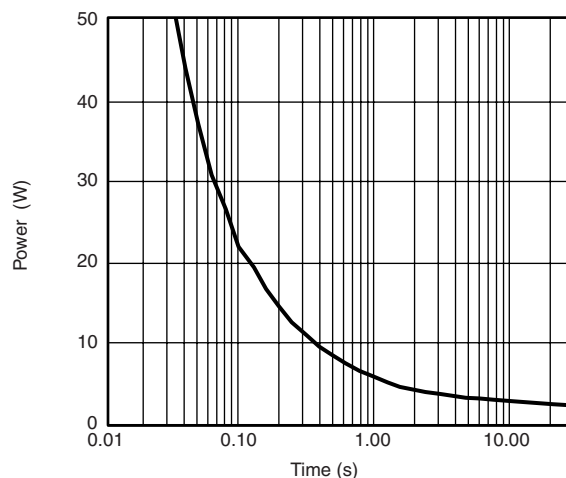
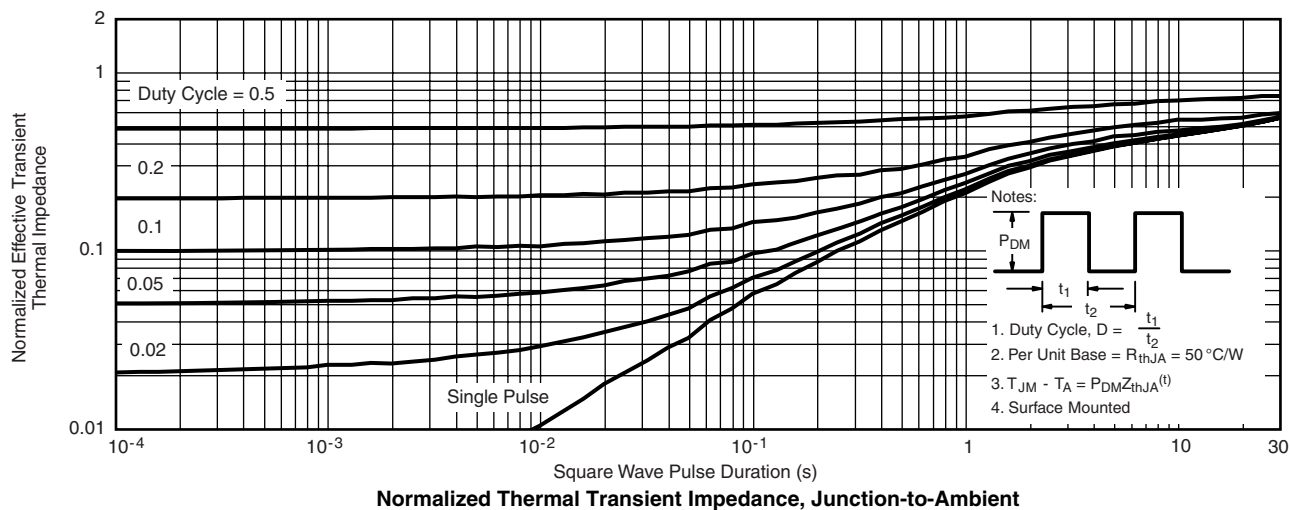
Capacitance



Gate Charge



On-Resistance vs. Junction Temperature

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power****Normalized Thermal Transient Impedance, Junction-to-Ambient**

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